





#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Features**

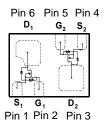
- Ultra Low Profile Package
- Low On-Resistance
- Very Low Gate Threshold Voltage, 0.9V Max.
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: X2-DFN1310-6
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208

#### X2-DFN1310-6





Top View Internal Schematic

## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN2005DLP4K-7	X2-DFN1310-6	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

DL

DL = Product Type Marking Code



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	20	V
Gate-Source Voltage		$V_{GSS}$	±10	V
Drain Current Per Element (Note 5)	Continuous Pulsed (Note 6)	I <sub>D</sub>	300 350	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	400	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	231	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

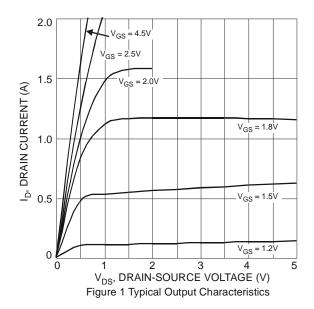
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

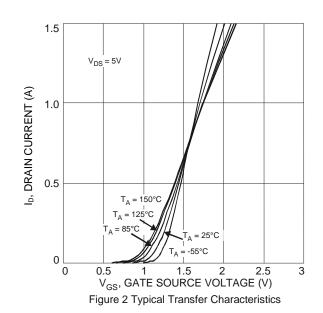
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Per Element) (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 100\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 17V$ , $V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±5	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Per Element) (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.53	_	0.9	V	$V_{DS} = V_{GS}$ , $I_D = 100\mu A$
		_	0.35	1.5		$V_{GS} = 4V, I_{D} = 10mA$
		_	0.4	1.7		$V_{GS} = 2.7V, I_D = 200mA$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	0.45	1.7	Ω	$V_{GS} = 2.5V, I_D = 10mA$
		_	0.55	3.5		$V_{GS} = 1.8V, I_D = 200mA$
		_	0.65	3.5		$V_{GS} = 1.5V, I_D = 1mA$
Forward Transfer Admittance	Y <sub>fs</sub>	40	_	_	mS	$V_{DS} = 3V, I_{D} = 10mA$

Notes: 5. Device mounted on FR-4 PCB.

6. Pulse width ≤10μS, Duty Cycle ≤1%.

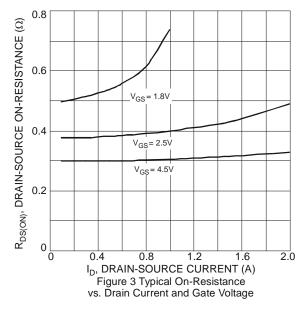
7. Short duration pulse test used to minimize self-heating effect.

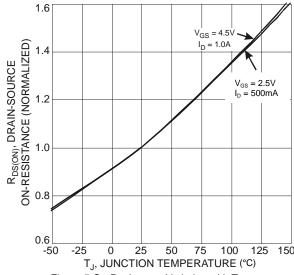


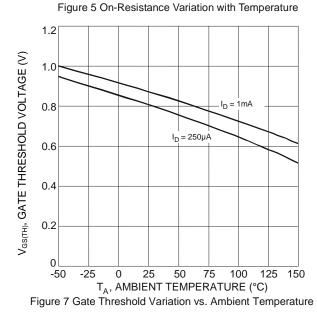












 $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$  $V_{GS} = 4.5V$ 0.6 T<sub>A</sub> = 150°C T<sub>A</sub> = 125°C 0.4  $T_A = 85^{\circ}C$ T<sub>A</sub> = 25°C 0.2  $T_A = -55$ °C 0 0 8.0 1.2 1.6  $I_D$ , DRAIN CURRENT (A) Figure 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

0.8

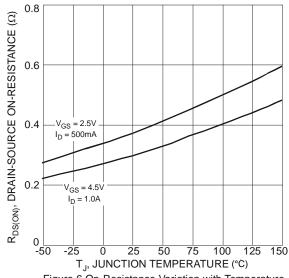


Figure 6 On-Resistance Variation with Temperature

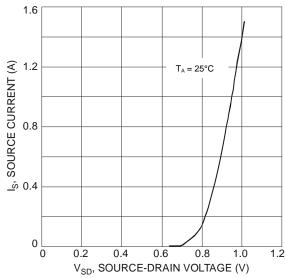
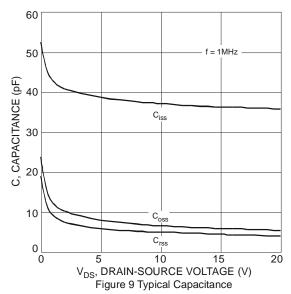


Figure 8 Diode Forward Voltage vs. Current

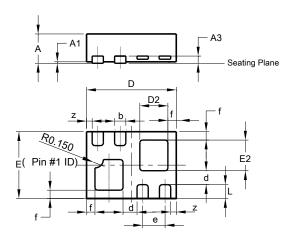




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN1310-6

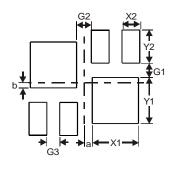


X2-DFN1310-6					
Dim	Min	Max	Тур		
Α	-	0.40	-		
A1	0	0.05	0.02		
A3	-	-	0.13		
b	0.10	0.20	0.15		
D	1.25	1.38	1.30		
d	-	-	0.25		
D2	0.30	0.50	0.40		
Е	0.95	1.075	1.00		
е	-	-	0.35		
E2	0.30	0.50	0.40		
f	-	-	0.10		
L	0.20	0.30	0.25		
Z	-	-	0.05		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X2-DFN1310-6



Dimensions	Value (in mm)
G1	0.16
G2	0.17
G3	0.15
X1	0.52
X2	0.20
Y1	0.52
Y2	0.375
а	0.09
b	0.06



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